

FOR COMPUTATIONAL MOLECULAR AND MATERIALS SCIENCE



Modeling Inter-layer Interactions in Layered Materials



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Outline

- Why layered materials?
- Levels of modeling.
- Classical intra- and inter-layer force fields.
- Applications of classical force-fields:
 - ✓ Structure of Graphene/h-BN hetero-structures.
 - ✓ Robust superlubricity in layered hetero-junctions.
 - ✓ Faceting in multi-walled nanotubes.
 - ✓ Inter-wall friction in CNTs and BNNTs.
- Electron transport across twisted graphene interfaces.
- Summary and outlook.

















Layered Materials at the Nanoscale

• A large family of materials



Layered Materials at the Nanoscale

Unique properties

- Controllable electronic properties.
- Enhanced mechanical rigidity.
- Structural anisotropy.
- Optical activity.
- Efficient heat transport.
- .

Possible applications

- Electronics and spintronics devices.
- Nano-electromechanical systems.
- Optics and communication.
- Tribology and solid lubrication.













Modeling Nanoscale Layered Materials

 At the nanoscale modeling and simulations are accurate and efficient.



Classical Force-Fields Construction



Classical Force-Fields

- Classical force-fields can be used to model many properties of layered materials:
 - ✓ Structural
 - ✓ Mechanical
 - ✓ Tribological
 - ✓ Heat transport
 - ✓ Chemical





- Layered materials are anisotropic by nature.
- Calls for a separate treatment of intra- and interlayer interactions.

Intra-Layer Potentials



- Intra-layer interactions are often modeled via:
 - ✓ Bonded two-body interactions (distances). $V_{ij} = k_{ij} (r_{ij} r_0)^2$
 - ✓ Bonded three-body interactions (angles). $V_{ijk} = k_{ijk} \left[\cos(\theta_{ijk}) \cos(\theta_0) \right]^2$
 - Bonded four-body interactions (dihedrals and Impropers).
- ✓ Van der Waals. $V_{vdw} = 4\varepsilon \left| \left(\frac{\sigma_{ij}}{r_{ij}} \right)^{12} \left(\frac{\sigma_{ij}}{r_{ij}} \right)^{6} \right|$ $V_{ijkl} = k_{ijkl} \left[1 + \cos \left(n_{ijkl} \phi_{ijkl} \phi_{0} \right) \right]$ ✓ Electrostatics. $V_{ijkl} = k_{ijkl} \left(\phi_{ijkl} - \phi_0 \right)^2$ $V_{Coul} = \frac{kq_iq_j}{r_j}$
- Examples:

Tersoff, Brenner, AIREBO, REAXFF, AMBER, CHARMM, MM4, ...



http://cbio.bmt.tue.nl/pumma/index.php/Theory/Potentials

Inter-Layer Potentials



- Inter-layer interactions often include:
 - ✓ Isotropic long-range dispersive attractions.
 - ✓ (An)isotropic short-range Pauli repulsions.
 - ✓ Electrostatics.
- Examples:

Lennard-Jones/Morse, Kolmogorov-Crespi, h-BN ILP, h-BN/graphene ILP

 A range-separation cutoff or a clear layer separation is required to apply the two terms simultaneously.

Isotropic Interlayer Potential for Graphene

- Isotropic potentials often provide a good description of the interlayer binding energy curve.
- However it predicts too shallow sliding energy curves.



M. Reguzzoni A. Fasolino E. Molinari and M. C. Righi, Potential energy surface for graphene on graphene. Phys. Rev. B 2012, 86, 245434.

Anisotropic Interlayer Potential for Graphene Kolmogorov & Crespi (KC)

 Pauli repulsions depend on the lateral distance between two atoms on adjacent layers as they cross each-other during the sliding process.



Kolmogorov, A. N.; Crespi, V. H., Registry-Dependent Interlayer Potential for Graphitic Systems. Phys. Rev. B 2005, 71, 235415.

Anisotropic Interlayer Potential for Graphene Kolmogorov & Crespi (KC)

• KC can describe both motions simultaneously for graphene.



M. Reguzzoni A. Fasolino E. Molinari and M. C. Righi, Potential energy surface for graphene on graphene. Phys. Rev. B 2012, 86, 245434.

Anisotropic Interlayer Potential for h-BN h-BN ILP

- *h*-BN ILP follows the spirit of the KC potential.
- vdW + repulsion:



damping term

- Coulomb interactions between partially charged atomic centers:
- vdW parameters taken from TS-vdW calculations. $E_{Coul} = k \frac{1}{\sqrt[3]{r_{ij}^3 + \left(\frac{1}{\lambda_{ii}}\right)^3}}$
- All parameters fine tuned against TS-vdW DFT.

Leven, I.; Azuri, I.; Kronik, L.; Hod, O., Inter-Layer Potential for Hexagonal Boron Nitride. J. Chem. Phys. 2014, 140, 104106

h-BN ILP performance - Binding



Leven, I.; Azuri, I.; Kronik, L.; Hod, O., Inter-Layer Potential for Hexagonal Boron Nitride. J. Chem. Phys. 2014, 140, 104106

h-BN ILP performance - Sliding



Leven, I.; Azuri, I.; Kronik, L.; Hod, O., Inter-Layer Potential for Hexagonal Boron Nitride. J. Chem. Phys. 2014, 140, 104106

Graphene/h-BN ILP



Same functional form as the h-BN ILP without Coulomb interactions.



I. Leven, T. Maaravi, I. Azuri, L. Kronik, and O. Hod, J. Chem. Theory Comput. 12, 2896-2905 (2016).

Classical Force-Fields Applications

Graphene/h-BN Heterojunctions



Graphene/h-BN Hetero-Structures

LETTERS PUBLISHED ONLINE: 14 JULY 2013 | DOI: 10.1038/NMAT3699

mature

Epitaxial growth of single-domain graphene on hexagonal boron nitride

Wei Yang¹, Guorui Chen², Zhiwen Shi¹, Cheng-Cheng Liu^{1,3}, Lianchang Zhang¹⁴, Guibai Xie¹, Meng Cheng¹, Duoming Wang¹, Rong Yang¹, Dongxia Shi¹, Kenji Watanabe⁵, Takashi Taniguchi⁵, Yugui Yao³, Yuanbo Zhang² and Guangyu Zhang^{1*}

Field-Effect Tunneling Transistor Based on Vertical Graphene Heterostructures

L. Britnell,¹ R. V. Gorbachev,² R. Jalil,² B. D. Belle,² F. Schedin,² A. Mishchenko,¹ T. Georgiou,³ M. I. Katsnelson,³ L. Eaves,⁴ S. V. Morozov,⁵ N. M. R. Peres,^{6,7} J. Leist,⁸ A. K. Geim,^{1,2}* K. S. Novoselov,¹* L. A. Ponomarenko¹*

LETTERS PUBLISHED ONLINE: 22 AUGUST 2010 | DOI: 10.1038/NNANO.2010.17

nature nanotechnology

Boron nitride substrates for high-quality graphene electronics

C. R. Dean^{1,2+}, A. F. Young¹, I. Meric¹, C. Lee^{4,5}, L. Wang², S. Sorgenfrei¹, K. Watanabe⁶, T. Taniguchi⁶, P. Kim³, K. L. Shepard¹ and J. Hone²⁺

LETTER

doi:10.1038/nature11408

Graphene and boron nitride lateral heterostructures for atomically thin circuitry

Mark P. Levendorf^{1*}, Cheol-Joo Kim^{1*}, Lola Brown¹, Pinshane Y. Huang², Robin W. Havener², David A. Muller^{2,3} & Jiwoong Park^{1,3}



LETTERS PUBLISHED ONLINE 22 JUNE 2015 | DOI: 10.1038/INNANO.2015.13

nature nanotechnology

Graphene on hexagonal boron nitride as a tunable hyperbolic metamaterial

S. Dai¹, Q. Ma², M. K. Liu¹³, T. Andersen², Z. Fei¹, M. D. Goldflam¹, M. Wagner¹, K. Watanabe⁴, T. Taniguchi⁴, M. Thiemens⁵, F. Keilmann⁶, G. C. A. M. Janssen⁷, S-E. Zhu⁷, P. Jarillo-Herrero², M. M. Fogler³ and D. N. Basov^{1*}

LETTERS PUBLISHED ONLINE: 13 FEBRUARY 2011 | DOI: 10.1038/NMAT2968 mature materials

Scanning tunnelling microscopy and spectroscopy of ultra-flat graphene on hexagonal boron nitride

Jiamin Xue¹, Javier Sanchez-Yamagishi², Danny Bulmash², Philippe Jacquod^{1,3}, Aparna Deshpande^{1†}, K. Watanabe⁴, T. Taniguchi⁴, Pablo Jarillo-Herrero² and Brian J. LeRoy^{1 *}





LETTER

doi:10.1038/nature12187

Cloning of Dirac fermions in graphene superlattices

L. A. Ponomarenko', R. V. Gorbachev², G. L. Yu¹, D. C. Elias¹, R. Jalli², A. A. Patel³, A. Mishchenko¹, A. S. Mayorov¹, C. R. Woods¹, J. R. Wallbank², M. Mucha-Kruczynski³, B. A. Piot^{*}, M. Potemski⁴, I. V. Grigorieva¹, K. S. Novoselov¹, F. Guinea⁵, V. I. Fal'ko³ & A. K. Geim¹²

nature physics

ARTICLES PUBLISHED ONLINE: 28 APRIL 2014 I DOI: 10.1038/NPH/VS2954

Commensurate-incommensurate transition in graphene on hexagonal boron nitride

C. R. Woods¹, L. Britnell¹, A. Eckmann², R. S. Ma³, J. C. Lu³, H. M. Guo³, X. Lin³, G. L. Yu¹, Y. Cao⁴, R. V. Gorbachev⁴, A. V. Kretinin¹, J. Park^{1,5}, L. A. Ponomarenko¹, M. I. Katsnelson⁶, Yu. N. Gornostyrev⁷, K. Watanabe⁸, T. Taniguchi⁸, C. Casiraghi², H-J. Gao³, A. K. Geim⁴ and K. S. Novoselov¹

. .

Massive Dirac Fermions and Hofstadter Butterfly in a van der Waals Heterostructure

B. Hunt,¹* J. D. Sanchez-Yamagishi,¹* A. F. Young,¹* M. Yankowitz,² B. J. LeRoy,² K. Watanabe,³ T. Taniguchi,³ P. Moon,⁴↑ M. Koshino,⁴ P. Jarillo-Herrero,¹‡ R. C. Ashoori¹‡

LETTER

doi:10.1038/nature12186

Hofstadter's butterfly and the fractal quantum Hall effect in moiré superlattices

C. R. Dean¹, L. Wang², P. Maher³, C. Forsythe³, F. Ghahari³, Y. Gao², J. Katoch⁴, M. Ishigami⁴, P. Moon⁵, M. Koshino⁵, T. Taniguchi⁶, K. Watanabe⁶, K. L. Shepard⁷, J. Hone² & P. Kim³

Graphene/h-BN Hetero-Structures

- Graphene and *h*-BN have an intralayer lattice mismatch of 1.83%.
- Moiré patterns result in domain walls.



Graphene/h-BN Hetero-Structures

 The number of layers and interlayer misfit angle dictate the relaxed structure.

0° Misfit angle

5 layers

2 layers

20° Misfit angle, bilayer





(b) $(c) \rightarrow (d) \rightarrow (d)$

Can nanoscale graphitic interfaces exhibit sustainable superlubric behavior?

PRL 100, 046102 (2008)

PHYSICAL REVIEW LETTERS

week ending 1 FEBRUARY 2008

Torque and Twist against Superlubricity

Alexander E. Filippov,¹ Martin Dienwiebel,^{2,3} Joost W. M. Frenken,² Joseph Klafter,⁴ and Michael Urbakh⁴

Nanoscale graphene flakes dynamically rotate and lock in the commensurate high friction state.



Robust Superlubricity in Graphene/h-BN Heterojunctions

Itai Leven, Dana Krepel, Ortal Shemesh, and Oded Hod*

Due to the intrinsic 1.8% lattice vector mismatch of the hexagonal lattices of graphene and *h*-BN their heterogeneous junction is expected to present superlubric behavior regardless of their relative orientation.



- Geometric modeling of rigid surfaces using the Registry Index method demonstrated that for large enough flakes robust superlubricity can be achieved by considerably reducing the PES (and hence friction) anisotropy.
- Neglecting dynamic effects!

Self orientation of graphene sandwiched between *h*-BN surfaces.

Evidence for a fractional fractal quantum Hall effect in graphene superlattices

Lei Wang^{1,2}, Yuanda Gao¹, Bo Wen³, Zheng Han³, Takashi Taniguchi⁴, Kenji Watanabe⁴, Mikito Koshino⁵, James Hone¹, ... + See all authors and affiliations

Science 04 Dec 2015: Vol. 350, Issue 6265, pp. 1231-1234 DOI: 10.1126/science.aad2102



Self orientation of graphene on *h*-BN.



Altmetric: 4 Views: 4,123 Citations: 6

More detail >>

Article | OPEN

Macroscopic self-reorientation of interacting two-dimensional crystals

C. R. Woods, F. Withers, M. J. Zhu, Y. Cao, G. Yu, A. Kozikov, M. Ben Shalom, S. V. Morozov, M. M. van Wijk, A. Fasolino, M. I. Katsnelson, K. Watanabe, T. Taniguchi, A. K. Geim, A. Mishchenko & K. S. Novoselov 🕿

Figure 1: Optical and atomic force microscopy of a self-rotating flake.



Multi-contact superlubricity in graphene/graphene and graphene/h-BN junctions.





Robust superlubricity in microscale graphene/*h***-BN heterostructures**



Some cool fully atomistic molecular dynamics simulations



Classical Force-Fields Applications

Nanotube Faceting



Faceting in Multi-Walled Nanotubes

- Nanotubes are often considered to have cylindrical cross sections.
- MWNTs can exhibit circumferential faceting.
- Faceting is more abundant in MWBNNTs than in MWCNTs.



Carbon





- 1. G. Zhang, X. Jiang, E. Wang, Science **300**, 472 (2003).
- 2. Y. Gogotsi, J. A. Libera, N. Kalashnikov, M. Yoshimura, Science 290, 317 (2000).
- 3. A. Celik-Aktas, J. Zuo, J. F. Stubbins, C. Tangc and Y. Bando, Acta Cryst. (2005). A61, 533.

Faceting in Multi-Walled Nanotubes

- Open questions:
 - ✓ Why do facets form?
 - ✓ What dictates the number of facets?
 - ✓ What determines the facet helicity?



- ✓ Why are facets more abundant in MWBNNTs than in MWCNTs?
- How does faceting influence the mechanical and tribological properties of MWNTs?

Nanotube Faceting and Local Registry

 The anisotropic interlayer potential of Kolmogorov and Crespi (Phys. Rev. B 71, 235415 (2005)) for graphitic systems and our h-BN-ILP (J. Chem. Phys. 140, 104106 (2014)) are used to perform geometry optimizations of double walled nanotubes.

I. Leven, R. Guerra, A. Vanossi, E. Tosatti, and O. Hod, "Multi-Walled Nanotube Faceting Unravelled", Nat. Nanotechnol. 11, 1082-1086 (2016).

- ✓ ZZ@ZZ and AC@AC DWNTs form facets.
- ✓ ZZ@AC do not facet.
- ✓ The critical diameter for faceting is 5-13 nm in agreement with experiment (*Nano Lett.* 12, 6347-6352 (2012)).
- ✓ Number of facets equals the difference in the number of circumferential unit cells.
- Local registry patterns reveal that the difference in circumferential unit cells distributes evenly around the nanotube.
- \checkmark Bad registry regions form vertices.





Chiral DWNT Nanotube Faceting

- Local registry patterns determine faceting in chiral DWNTs, as well.
- Mono-chiral DWNTs form non-uniform axial patterns.



• The interlayer spacing is close to equilibrium at the facets and increases at the vertices. $\Delta \theta = 0^{\circ}$ $\Delta \theta = 0.252^{\circ}$ $\Delta \theta = 0.657^{\circ}$ $\Delta \theta = 1.14^{\circ}$ $\Delta \theta = 1.74^{\circ}$ LRI G Initial: LRI **Relaxed: IL** spacing **Relaxed:**

I. Leven, R. Guerra, A. Vanossi, E. Tosatti, and O. Hod, "Multi-Walled Nanotube Faceting Unravelled", Nat. Nanotechnol. 11, 1082-1086 (2016).



Science, 290, 317 (2000)

Why is faceting more abundant in BNNTs than in CNTs?

- Faceting requires chiral angle matching between adjacent layer.
- MWBNNTs present high uniformity in the chirality of the different layers whereas MWCNTs have a much wider distribution of wall chiralities.
- This is a result of the larger interlayer adhesion in *h*-BN and the weak, yet important (when summed over large surfaces), electrostatic interactions between the partially charged atomic centers in BNNT that is absent in CNTs.



Classical Force-Fields Applications

Nanotube Friction

Enhance Friction in MWBNNTs

LETTERS PUBLISHED ONLINE: 1 JUNE 2014 | DOI: 10.1038/NMAT3985 mature materials

Ultrahigh interlayer friction in multiwalled boron nitride nanotubes

A. Niguès¹, A. Siria^{1*}, P. Vincent¹, P. Poncharal¹ and L. Bocquet^{1,2}

688 NATURE MATERIALS | VOL 13 | JULY 2014 | www.nature.com/naturematerials



Facet Superstructure Reconfiguration

Inter-wall pullout can cause facet superstructure reconfiguration

AC (75,75)@(80,80) DWCNT







Facet Superstructure Reconfiguration Telescopic motion of bi-chiral DWBNNT



Faceting Induced Friction



Conclusions

- Dedicated inter-layer force-fields have been developed for h-BN and graphene/h-BN.
- Inter-layer registry patterns dictate the super-structure of domain-wall formation in graphene/h-BN and faceting in multi-walled nanotubes.
- These are manifested in their tribological characteristics.
- Cross-layer transport is also highly dependent on the inter-layer registry.
- The force-field is transferable to other 2D materials.









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And you For your attention!

